

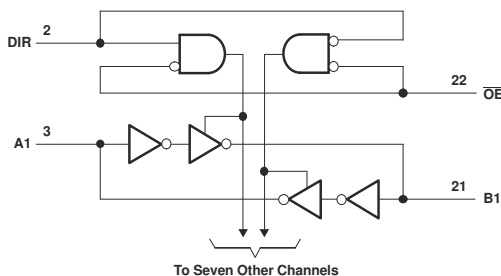
SN74LVC8T245 8 ビット デュアル電源バス・トランシーバ、 構成可能電圧変換、3 ステート出力

1 特長

- 制御入力の V_{IH}/V_{IL} レベルは V_{CCA} 電圧基準
- V_{CC} 絶縁機能: いずれかの V_{CC} 入力 が GND レベルになると、すべてが高インピーダンス状態に移行
- 完全に構成可能なデュアル・レール設計により、1.65V ~ 5.5V の電源電圧の全範囲にわたって各ポートが動作可能
- JESD 78, Class II 準拠で 100mA 超のラッチアップ性能
- JESD 22 を上回る ESD 保護
 - 4000V、人体モデル (A114-A)
 - 100V、マシン・モデル (A115-A)
 - 1000V、デバイス帯電モデル (C101)

2 アプリケーション

- パーソナル・エレクトロニクス
- 産業用
- エンタープライズ
- 通信機器



論理図 (正論理)

3 概要

SN74LVC8T245 は、8 ビット非反転バス・トランシーバであり、双方向の電圧レベル変換を可能にする構成可能なデュアル電源レールを備えています。SN74LVC8T245 は、 V_{CCA} および V_{CCB} が 1.65V ~ 5.5V に設定された状態で動作するよう最適化されています。A ポートは V_{CCA} に追従するように設計されており、 V_{CCA} は 1.65V ~ 5.5V の電源電圧に対応します。B ポートは V_{CCB} に追従するように設計されており、 V_{CCB} は 1.65V ~ 5.5V の電源電圧に対応します。このため、1.8V、2.5V、3.3V、5V の任意の電圧ノード間での自在な低電圧双方向変換が可能です。

SN74LVC8T245 は、2 つのデータ・バス間の非同期通信用に設計されています。方向制御 (DIR) 入力および出力イネーブル (\overline{OE}) 入力のロジック・レベルに応じて、B ポート出力もしくは A ポート出力のいずれかがアクティブになるか、または、両方の出力ポートが高インピーダンス・モードになります。本デバイスは、B ポート出力がアクティブになった場合、A バスから B バスへデータを転送し、A ポート出力がアクティブになった場合、B バスから A バスへデータを転送します。A ポートと B ポートの入力回路はどちらも常にアクティブであるため、これらのポートには論理 HIGH または LOW レベルを印加して、 I_{CC} と I_{CCZ} が過剰に流れないようにする必要があります。

このデバイスは、 I_{off} を使用する部分的パワーダウン・アプリケーション用の動作が完全に規定されています。 I_{off} 回路が出力をディセーブルにするため、電源切断時にデバイスに電流が逆流して損傷に至ることを回避できます。 V_{CC} 絶縁機能は、どちらかの V_{CC} 入力 が GND レベルになると、全ての出力を確実に高インピーダンス状態にします。電源オンまたは電源オフ時に高インピーダンス状態を確保するため、 \overline{OE} はプルアップ抵抗経路で V_{CC} に接続する必要があります。この抵抗の最小値は、ドライバの電流シンク能力によって決定されます。

SN74LVC8T245 は、制御ピン (DIR および \overline{OE}) が V_{CCA} から電源を供給されるように設計されています。

パッケージ情報

部品番号	パッケージ (1)	本体サイズ (公称)
SN74LVC8T245	DBV (SSOP, 24)	8.20mm × 5.30mm
	DBQ (SSOP, 24)	8.65mm × 3.90mm
	PW (TSSOP, 24)	7.80mm × 4.40mm
	DGV (TVSOP, 24)	5.00mm × 4.40mm
	RHL (VQFN, 24)	5.50mm × 3.50mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision B (November 2014) to Revision C (December 2022)	Page
• マシン・モデルの仕様を削除.....	1
• 文書全体にわたって表、図、相互参照の採番方法を更新.....	1
• Updated the <i>ESD Ratings</i> section (was called <i>Handling Ratings</i>).....	5
• Updated thermals in the Thermal Informations section.	7
• Increased max switching characteristics specs for $V_{CCB} = 5\text{V}$	9
• Updated the <i>Overview</i> section.....	13
• Added the <i>Balanced High-Drive CMOS Push-Pull Outputs</i> and <i>V_{CC} Isolation</i> sections.....	13
• Updated the <i>Power Supply Recommendations</i> section.....	16

Changes from Revision A (June 2005) to Revision B (November 2014)	Page
• 「アプリケーション」リスト、「ピン機能」表、「取り扱いに関する定格」表、「機能説明」セクション、「デバイスの機能モード」セクション、「アプリケーションと実装」セクション、「電源に関する推奨事項」セクション、「レイアウト」セクション、「デバイスおよびドキュメントのサポート」セクション、「メカニカル、パッケージ、および注文情報」セクションを追加	1
• 「特長」の「200V、マシン・モデル (A115-A)」を「100V、マシン・モデル (A115-A)」に変更.....	1

Changes from Revision * (June 2005) to Revision A (August 2005)	Page
• デバイスを「製品プレビュー」から「量産」に変更.....	1

5 Pin Configuration and Functions

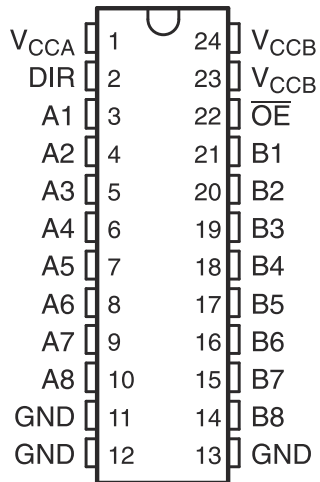


图 5-1. DW, NS, DB, DBQ, DGV, or PW Package, 24-Pin SOIC, SO, SSOP, SSOP, TVSOP, or TSSOP (Top View)

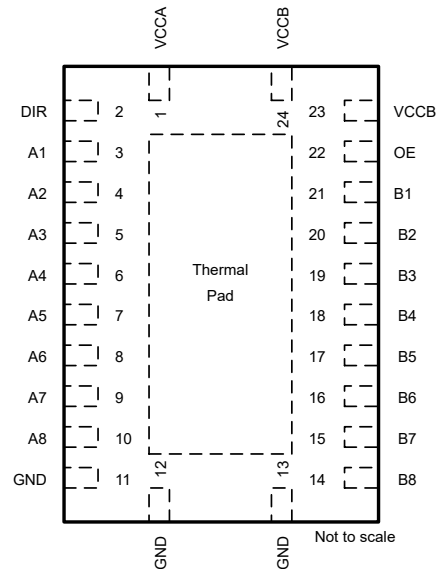


图 5-2. RHL Package, 24-Pin VQFN (Top View)

表 5-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
A1	3	I/O	Input/output A1. Referenced to V_{CCA} .
A2	4	I/O	Input/output A2. Referenced to V_{CCA} .
A3	5	I/O	Input/output A3. Referenced to V_{CCA} .
A4	6	I/O	Input/output A4. Referenced to V_{CCA} .
A5	7	I/O	Input/output A5. Referenced to V_{CCA} .
A6	8	I/O	Input/output A6. Referenced to V_{CCA} .
A7	9	I/O	Input/output A7. Referenced to V_{CCA} .
A8	10	I/O	Input/output A8. Referenced to V_{CCA} .
B1	21	I/O	Input/output B1. Referenced to V_{CCB} .
B2	20	I/O	Input/output B2. Referenced to V_{CCB} .
B3	19	I/O	Input/output B3. Referenced to V_{CCB} .
B4	18	I/O	Input/output B4. Referenced to V_{CCB} .
B5	17	I/O	Input/output B5. Referenced to V_{CCB} .
B6	16	I/O	Input/output B6. Referenced to V_{CCB} .
B7	15	I/O	Input/output B7. Referenced to V_{CCB} .
B8	14	I/O	Input/output B8. Referenced to V_{CCB} .
DIR	2	I	Direction-control signal.
GND	11, 12, 13	G	Ground
\overline{OE}	22	I	3-state output-mode enables. Pull \overline{OE} high to place all outputs in 3-state mode. Referenced to V_{CCA} .
V_{CCA}	1	P	A-port supply voltage. $1.65\text{ V} \leq V_{CCA} \leq 5.5\text{ V}$
V_{CCB}	23, 24	P	B-port supply voltage. $1.65\text{ V} \leq V_{CCB} \leq 5.5\text{ V}$
Thermal Pad ⁽²⁾		—	

(1) I = input, O = output, P = power

(2) For the RHL package only

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)

(1)		MIN	MAX	UNIT	
Supply voltage range, V_{CCA} , V_{CCB}		-0.5	6.5	V	
V_I	Input voltage range ⁽²⁾	I/O ports (A port)	-0.5	6.5	V
		I/O ports (B port)	-0.5	6.5	
		Control inputs	-0.5	6.5	
V_O	Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾	A port	-0.5	6.5	V
		B port	-0.5	6.5	
V_O	Voltage range applied to any output in the high or low state ^{(2) (3)}	A port	-0.5	$V_{CCA} + 0.5$	V
		B port	-0.5	$V_{CCB} + 0.5$	
I_{IK}	Input clamp current	$V_I < 0$	-50	mA	
I_{OK}	Output clamp current	$V_O < 0$	-50	mA	
I_O	Continuous output current		±50	mA	
	Continuous current through each V_{CCA} , V_{CCB} , and GND		±100	mA	
T_{stg}	Storage temperature	-65	150	°C	
T_J	Junction temperature		150	°C	

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The output positive-voltage rating may be exceeded up to 6.5 V maximum if the output current rating is observed.

6.2 ESD Ratings

			MIN	MAX	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	-4000	4000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	-1000	1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

(1) (2) (3) (4)			V _{CCI}	V _{CCO}	MIN	MAX	UNIT
V _{CCA}	Supply voltage				1.65	5.5	V
V _{CCB}					1.65	5.5	
V _{IH}	High-level input voltage	Data inputs ⁽⁵⁾	1.65 V to 1.95 V		V _{CCI} × 0.65		V
			2.3 V to 2.7 V		1.7		
			3 V to 3.6 V		2		
			4.5 V to 5.5 V		V _{CCI} × 0.7		
V _{IL}	Low-level input voltage	Data inputs ⁽⁵⁾	1.65 V to 1.95 V			V _{CCI} × 0.35	V
			2.3 V to 2.7 V			0.7	
			3 V to 3.6 V			0.8	
			4.5 V to 5.5 V			V _{CCI} × 0.3	
V _{IH}	High-level input voltage	Control inputs (referenced to V _{CCA}) ⁽⁶⁾	1.65 V to 1.95 V		V _{CCA} × 0.65		V
			2.3 V to 2.7 V		1.7		
			3 V to 3.6 V		2		
			4.5 V to 5.5 V		V _{CCA} × 0.7		
V _{IL}	Low-level input voltage	Control inputs (referenced to V _{CCA}) ⁽⁶⁾	1.65 V to 1.95 V			V _{CCA} × 0.35	V
			2.3 V to 2.7 V			0.7	
			3 V to 3.6 V			0.8	
			4.5 V to 5.5 V			V _{CCA} × 0.3	
V _I	Input voltage	Control inputs			0	5.5	V
V _{I/O}	Input/output voltage	Active state			0	V _{CCO}	V
		3-State			0	5.5	V
I _{OH}	High-level output current			1.65 V to 1.95 V		–4	mA
				2.3 V to 2.7 V		–8	
				3 V to 3.6 V		–24	
				4.5 V to 5.5 V		–32	
I _{OL}	Low-level output current			1.65 V to 1.95 V		4	mA
				2.3 V to 2.7 V		8	
				3 V to 3.6 V		24	
				4.5 V to 5.5 V		32	
Δt/Δv ⁽⁷⁾	Input transition rise or fall rate	Data inputs	1.65 V to 1.95 V			20	ns/V
			2.3 V to 2.7 V			20	
			3 V to 3.6 V			10	
			4.5 V to 5.5 V			5	
T _A	Operating free-air temperature				–40	85	°C

(1) V_{CCI} is the V_{CC} associated with the data input port.

(2) V_{CCO} is the V_{CC} associated with the output port.

(3) All unused or driven (floating) data inputs (I/Os) of the device must be held at logic HIGH or LOW (preferably V_{CCI} or GND) to ensure proper device operation and minimize power. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

(4) All unused control inputs must be held at V_{CCA} or GND to ensure proper device operation and minimize power consumption.

(5) For V_{CCI} values not specified in the data sheet, V_{IH} min = V_{CCI} × 0.7 V, V_{IL} max = V_{CCI} × 0.3 V.

(6) For V_{CCA} values not specified in the data sheet, V_{IH} min = V_{CCA} × 0.7 V, V_{IL} max = V_{CCA} × 0.3 V.

(7) Maximum input transition rate with < 4 channels switching simultaneously.

6.4 Thermal Information DB, DBQ and DGV

THERMAL METRIC ⁽¹⁾		DB	DBQ	DGV	UNIT
		24 PINS	24 PINS	24 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	90.7	81.2	91.1	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	51.9	44.8	23.7	
R _{θJB}	Junction-to-board thermal resistance	49.7	34.5	44.5	
ψ _{JT}	Junction-to-top characterization parameter	18.8	9.5	0.6	
ψ _{JB}	Junction-to-board characterization parameter	49.3	37.2	44.1	
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Thermal Information PW and RHL

THERMAL METRIC ⁽¹⁾		PW	RHL	UNIT
		24 PINS	24 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	100.6	48.3	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	44.7	46.1	
R _{θJB}	Junction-to-board thermal resistance	55.8	26.1	
ψ _{JT}	Junction-to-top characterization parameter	6.8	4.6	
ψ _{JB}	Junction-to-board characterization parameter	55.4	26.0	
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	15.7	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

6.6 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER ^{(1) (2)}		TEST CONDITIONS	V _{CCA}	V _{CCB}	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
V _{OH}		I _{OH} = -100 μA, V _I = V _{IH}	1.65 V to 4.5 V	1.65 V to 4.5 V				V _{CCO} - 0.1			V	
		I _{OH} = -4 mA, V _I = V _{IH}	1.65 V	1.65 V				1.2				
		I _{OH} = -8 mA, V _I = V _{IH}	2.3 V	2.3 V				1.9				
		I _{OH} = -24 mA, V _I = V _{IH}	3 V	3 V				2.4				
		I _{OH} = -32 mA, V _I = V _{IH}	4.5 V	4.5 V				3.8				
V _{OL}		I _{OL} = 100 μA, V _I = V _{IL}	1.65 V to 4.5 V	1.65 V to 4.5 V						0.1	V	
		I _{OL} = 4 mA, V _I = V _{IL}	1.65 V	1.65 V						0.45		
		I _{OL} = 8 mA, V _I = V _{IL}	2.3 V	2.3 V						0.3		
		I _{OL} = 24 mA, V _I = V _{IL}	3 V	3 V						0.55		
		I _{OL} = 32 mA, V _I = V _{IL}	4.5 V	4.5 V						0.55		
I _I	DIR	V _I = V _{CCA} or GND	1.65 V to 5.5 V	1.65 V to 5.5 V						±1	±2	μA
I _{off}	A or B port	V _I or V _O = 0 to 5.5 V	0 V	0 to 5.5 V						±1	±2	μA
			0 to 5.5 V	0 V						±1	±2	
I _{OZ}	A or B port	V _O = V _{CCO} or GND, OE = V _{IH}	1.65 V to 5.5 V	1.65 V to 5.5 V						±1	±2	μA
I _{CCA}		V _I = V _{CCI} or GND, I _O = 0	1.65 V to 5.5 V	1.65 V to 5.5 V							15	μA
			5 V	0 V							15	
			0 V	5 V							-2	
I _{CCB}		V _I = V _{CCI} or GND, I _O = 0	1.65 V to 5.5 V	1.65 V to 5.5 V							15	μA
			5 V	0 V							-2	
			0 V	5 V							15	
I _{CCA} + I _{CCB}		V _I = V _{CCI} or GND, I _O = 0	1.65 V to 5.5 V	1.65 V to 5.5 V							25	μA
ΔI _{CCA}	A port	One A port at V _{CCA} - 0.6 V, DIR at V _{CCA} , B port = open	3 V to 5.5 V	3 V to 5.5 V							50	μA
	DIR	DIR at V _{CCA} - 0.6 V, B port = open, A port at V _{CCA} or GND									50	
ΔI _{CCB}	B port	One B port at V _{CCB} - 0.6 V, DIR at GND, A port = open	3 V to 5.5 V	3 V to 5.5 V							50	μA
C _i	Control inputs	V _I = V _{CCA} or GND	3.3 V	3.3 V			4				5	pF
C _{io}	A or B port	V _O = V _{CCA/B} or GND	3.3 V	3.3 V			8.5				10	pF

(1) V_{CCO} is the V_{CC} associated with the output port.

(2) V_{CCI} is the V_{CC} associated with the input port.

6.7 Switching Characteristics, $V_{CCA} = 1.8\text{ V} \pm 0.15\text{ V}$

over recommended operating free-air temperature range, $V_{CCA} = 1.8\text{ V} \pm 0.15\text{ V}$ (unless otherwise noted) (see [7-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CCB} = 1.8\text{ V} \pm 0.15\text{ V}$		$V_{CCB} = 2.5\text{ V} \pm 0.2\text{ V}$		$V_{CCB} = 3.3\text{ V} \pm 0.3\text{ V}$		$V_{CCB} = 5\text{ V} \pm 0.5\text{ V}$		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	1.7	21.9	1.3	9.2	1	7.4	0.8	7.1	ns
t_{PHL}											
t_{PLH}	B	A	0.9	23.8	0.8	23.6	0.7	23.4	0.7	23.4	ns
t_{PHL}											
t_{PHZ}	\overline{OE}	A	1.5	29.6	1.5	29.4	1.5	29.3	1.4	29.2	ns
t_{PLZ}											
t_{PHZ}	\overline{OE}	B	2.4	32.2	1.9	13.1	1.7	12	1.3	10.3	ns
t_{PLZ}											
t_{PZH}	\overline{OE}	A	0.4	24	0.4	23.8	0.4	23.7	0.4	23.7	ns
t_{PZL}											
t_{PZH}	\overline{OE}	B	1.8	32	1.5	16	1.2	12.6	0.9	12	ns
t_{PZL}											

6.8 Switching Characteristics, $V_{CCA} = 2.5\text{ V} \pm 0.2\text{ V}$

over recommended operating free-air temperature range, $V_{CCA} = 2.5\text{ V} \pm 0.2\text{ V}$ (unless otherwise noted) (see [7-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CCB} = 1.8\text{ V} \pm 0.15\text{ V}$		$V_{CCB} = 2.5\text{ V} \pm 0.2\text{ V}$		$V_{CCB} = 3.3\text{ V} \pm 0.3\text{ V}$		$V_{CCB} = 5\text{ V} \pm 0.5\text{ V}$		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	1.5	21.4	1.2	9	0.8	6.2	0.6	4.8	ns
t_{PHL}											
t_{PLH}	B	A	1.2	9.3	1	9.1	1	8.9	0.9	8.8	ns
t_{PHL}											
t_{PHZ}	\overline{OE}	A	1.4	9	1.4	9	1.4	9	1.4	9	ns
t_{PLZ}											
t_{PHZ}	\overline{OE}	B	2.3	29.6	1.8	11	1.7	9.3	0.9	6.9	ns
t_{PLZ}											
t_{PZH}	\overline{OE}	A	1	10.9	1	10.9	1	10.9	1	10.9	ns
t_{PZL}											
t_{PZH}	\overline{OE}	B	1.7	28.2	1.5	12.9	1.2	9.4	1	7.5	ns
t_{PZL}											

6.9 Switching Characteristics, $V_{CCA} = 3.3 \text{ V} \pm 0.3 \text{ V}$

over recommended operating free-air temperature range, $V_{CCA} = 3.3 \text{ V} \pm 0.3 \text{ V}$ (unless otherwise noted) (see [7-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CCB} = 1.8 \text{ V} \pm 0.15 \text{ V}$		$V_{CCB} = 2.5 \text{ V} \pm 0.2 \text{ V}$		$V_{CCB} = 3.3 \text{ V} \pm 0.3 \text{ V}$		$V_{CCB} = 5 \text{ V} \pm 0.5 \text{ V}$		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	1.5	21.2	1.1	8.8	0.8	6.3	0.5	4.4	ns
t_{PHL}											
t_{PLH}	B	A	0.8	7.2	0.8	6.2	0.7	6.1	0.6	6	ns
t_{PHL}											
t_{PHZ}	\overline{OE}	A	1.6	8.2	1.6	8.2	1.6	8.2	1.6	8.2	ns
t_{PLZ}											
t_{PHZ}	\overline{OE}	B	2.1	29	1.7	10.3	1.5	8.6	0.8	6.3	ns
t_{PLZ}											
t_{PZH}	\overline{OE}	A	0.8	8.1	0.8	8.1	0.8	8.1	0.8	8.1	ns
t_{PZL}											
t_{PZH}	\overline{OE}	B	1.8	27.7	1.4	12.4	1.1	8.8	0.9	6.8	ns
t_{PZL}											

6.10 Switching Characteristics, $V_{CCA} = 5 \text{ V} \pm 0.5 \text{ V}$

over recommended operating free-air temperature range, $V_{CCA} = 5 \text{ V} \pm 0.5 \text{ V}$ (unless otherwise noted) (see [7-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$		$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	1.5	21.4	1	8.8	0.7	6	0.4	4.2	ns
t_{PHL}											
t_{PLH}	B	A	0.7	7	0.4	4.8	0.3	4.5	0.3	4.3	ns
t_{PHL}											
t_{PHZ}	\overline{OE}	A	0.3	5.4	0.3	5.4	0.3	5.4	0.3	5.4	ns
t_{PLZ}											
t_{PHZ}	\overline{OE}	B	2	28.7	1.6	9.7	1.4	8	0.7	5.7	ns
t_{PLZ}											
t_{PZH}	\overline{OE}	A	0.7	6.4	0.7	6.4	0.7	6.4	0.7	6.4	ns
t_{PZL}											
t_{PZH}	\overline{OE}	B	1.5	27.6	1.3	11.4	1	8.8	0.9	6.6	ns
t_{PZL}											

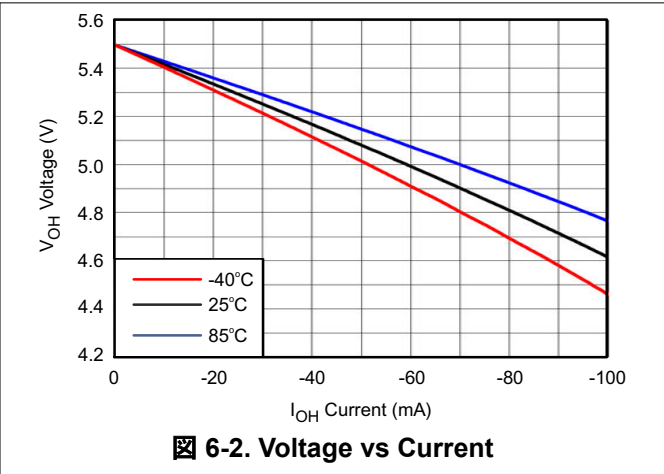
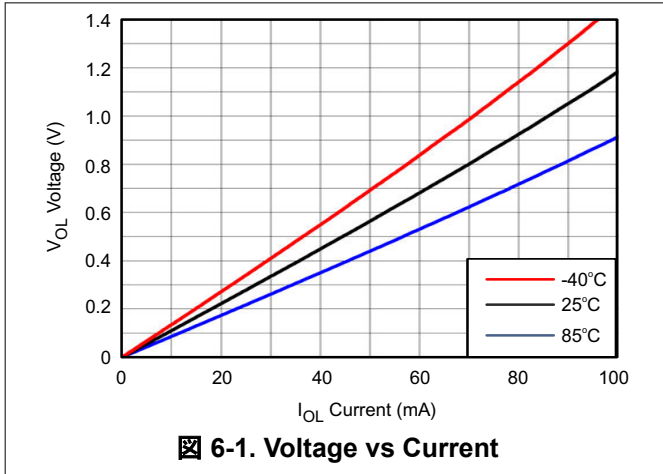
6.11 Operating Characteristics

$T_A = 25^\circ\text{C}$

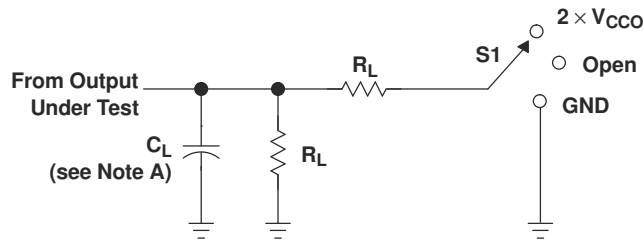
PARAMETER	TEST CONDITIONS	$V_{CCA} = V_{CCB} = 1.8 \text{ V}$	$V_{CCA} = V_{CCB} = 2.5 \text{ V}$	$V_{CCA} = V_{CCB} = 3.3 \text{ V}$	$V_{CCA} = V_{CCB} = 5 \text{ V}$	UNIT
		TYP	TYP	TYP	TYP	
C_{pdA} ⁽¹⁾	A-port input, B-port output	2	2	2	3	pF
	B-port input, A-port output	12	13	13	16	
C_{pdB} ⁽¹⁾	A-port input, B-port output	13	13	14	16	
	B-port input, A-port output	2	2	2	3	

(1) Power dissipation capacitance per transceiver

6.12 Typical Characteristics



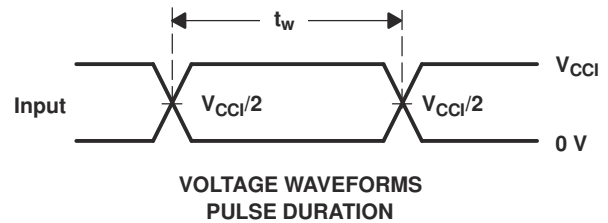
7 Parameter Measurement Information



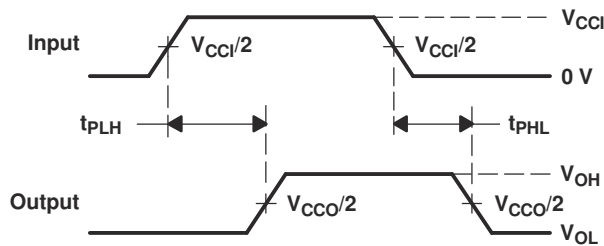
LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CCO}$
t_{PHZ}/t_{PZH}	GND

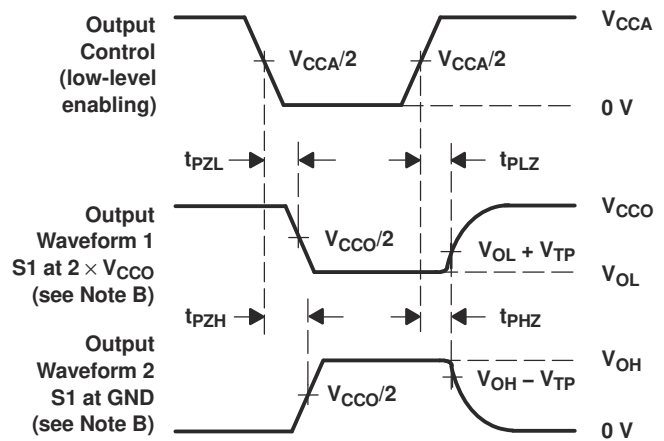
V_{CCO}	C_L	R_L	V_{TP}
$1.8\text{ V} \pm 0.15\text{ V}$	15 pF	2 k Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	15 pF	2 k Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	15 pF	2 k Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	15 pF	2 k Ω	0.3 V



VOLTAGE WAVEFORMS PULSE DURATION



VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES

- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $dv/dt \geq 1\text{ V/ns}$.
 - D. The outputs are measured one at a time, with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .
 - H. V_{CC1} is the V_{CC} associated with the input port.
 - I. V_{CCO} is the V_{CC} associated with the output port.
 - J. All parameters and waveforms are not applicable to all devices.

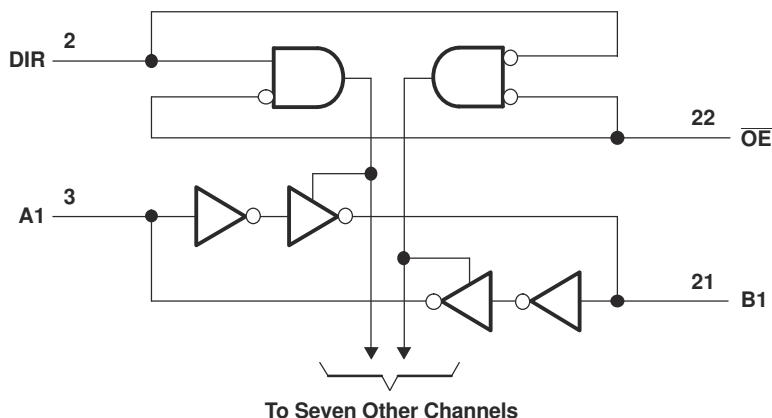
 **7-1. Load Circuit and Voltage Waveforms**

8 Detailed Description

8.1 Overview

The SN74LVC8T245 is an eight bit non-inverting bus transceiver with configurable dual power supply rails that enables bidirectional voltage level translation. Pin Ax and direction control pin are support by V_{CCA} and pin Bx is support by V_{CCB} . The A port is able to accept I/O voltages ranging from 1.65 V to 5.5 V, while the B port can accept I/O voltages from 1.65 V to 5.5 V. The high on DIR allows data transmission from A to B and a low on DIR allows data transmission from B to A. For voltage level translation below 1.65 V, see TI [AXC](#) products.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Fully Configurable Dual-Rail Design Allows Each Port to Operate Over the Full 1.65-V to 5.5-V Power-Supply Range

Both V_{CCA} and V_{CCB} can be supplied at any voltage between 1.65 V and 5.5 V making the device suitable for translating between any of the voltage nodes (1.8 V, 2.5 V, 3.3 V, and 5 V).

8.3.2 I_{off} Supports Partial-Power-Down Mode Operation

I_{off} prevents backflow current by disabling I/O output circuits when device is in partial-power-down mode. The inputs and outputs for this device enter a high-impedance state when the device is powered down, inhibiting current backflow into the device. The maximum leakage into or out of any input or output pin on the device is specified by I_{off} in the Electrical Characteristics.

8.3.3 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. Two outputs can be connected together for 2X stronger output drive strength. The electrical and thermal limits defined in the Absolute Maximum Ratings must be followed at all times.

8.3.4 V_{CC} Isolation

The I/O's of both ports will enter a high-impedance state when either of the supplies are at GND, while the other supply is still connected to the device. The maximum leakage into or out of any input or output pin on the device is specified by I_{off} in the *Electrical Characteristics*.

8.4 Device Functional Modes

The SN74LVC8T245 is voltage level translator that can operate from 1.65 V to 5.5 V (V_{CCA} and V_{CCB}). The signal translation between 1.65 V and 5.5 V requires direction control and output enable control. When \overline{OE} is low and DIR is high, data transmission is from A to B. When \overline{OE} is low and DIR is low, data transmission is from B to A. When \overline{OE} is high, both output ports will be high-impedance. For voltage level translation below 1.65V, see TI [AXC](#) products.

**表 8-1. Function Table
(Each 8-Bit Section)**

CONTROL INPUTS ⁽¹⁾		OUTPUT CIRCUITS		OPERATION
\overline{OE}	DIR	A PORT	B PORT	
L	L	Enabled	Hi-Z	B data to A bus
L	H	Hi-Z	Enabled	A data to B bus
H	X	Hi-Z	Hi-Z	Isolation

(1) Input circuits of the data I/Os are always active.

9 Application and Implementation

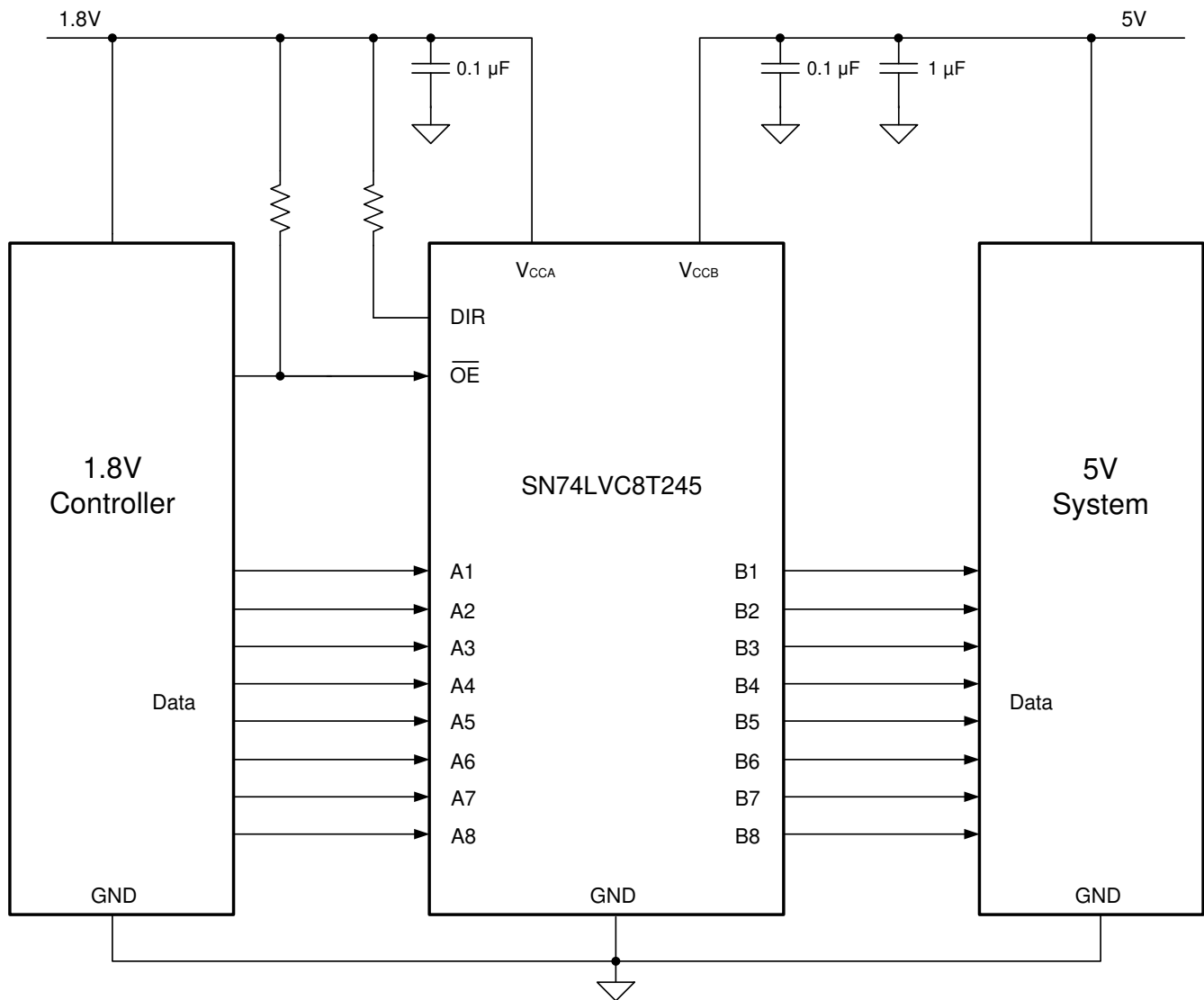
注

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9.1 Application Information

The SN74LVC8T245 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The maximum output current can be up to 32 mA when device is powered by 5 V. It is recommended to tie all unused I/Os to GND. The device should not have any floating I/Os when changing translation direction.

9.2 Typical Application



☒ 9-1. Typical Application Circuit

9.2.1 Design Requirements

For this design example, use the parameters listed in 表 9-1.

表 9-1. Design Parameters

PARAMETERS	VALUES
Input voltage range	1.65 V to 5.5 V
Output voltage	1.65 V to 5.5 V

9.2.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
 - Use the supply voltage of the device that is driving the SN74LVC8T245 device to determine the input voltage range. For a valid logic high, the value must exceed the V_{IH} of the input port. For a valid logic low, the value must be less than the V_{IL} of the input port.
- Output voltage range
 - Use the supply voltage of the device that the SN74LVC8T245 device is driving to determine the output voltage range.

9.2.3 Application Curve

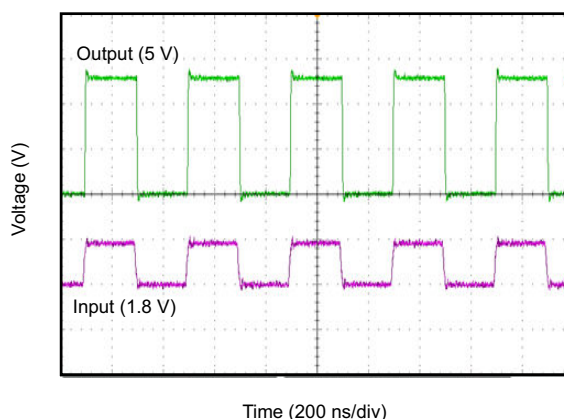


图 9-2. Translation Up (1.8 V to 5 V) at 2.5 MHz

10 Power Supply Recommendations

The SN74LVC8T245 device uses two separate configurable power-supply rails, V_{CCA} and V_{CCB} . V_{CCA} accepts any supply voltage from 1.65 V to 5.5 V and V_{CCB} accepts any supply voltage from 1.65 V to 5.5 V. The A port and B port are designed to track V_{CCA} and V_{CCB} respectively allowing for low-voltage bidirectional translation between any of the 1.8-V, 2.5 -V, 3.3-V and 5-V voltage nodes. The recommendation is to first power-up the input supply rail to help avoid internal floating while the output supply rail ramps up. However, both power-supply rails can be ramped up simultaneously.

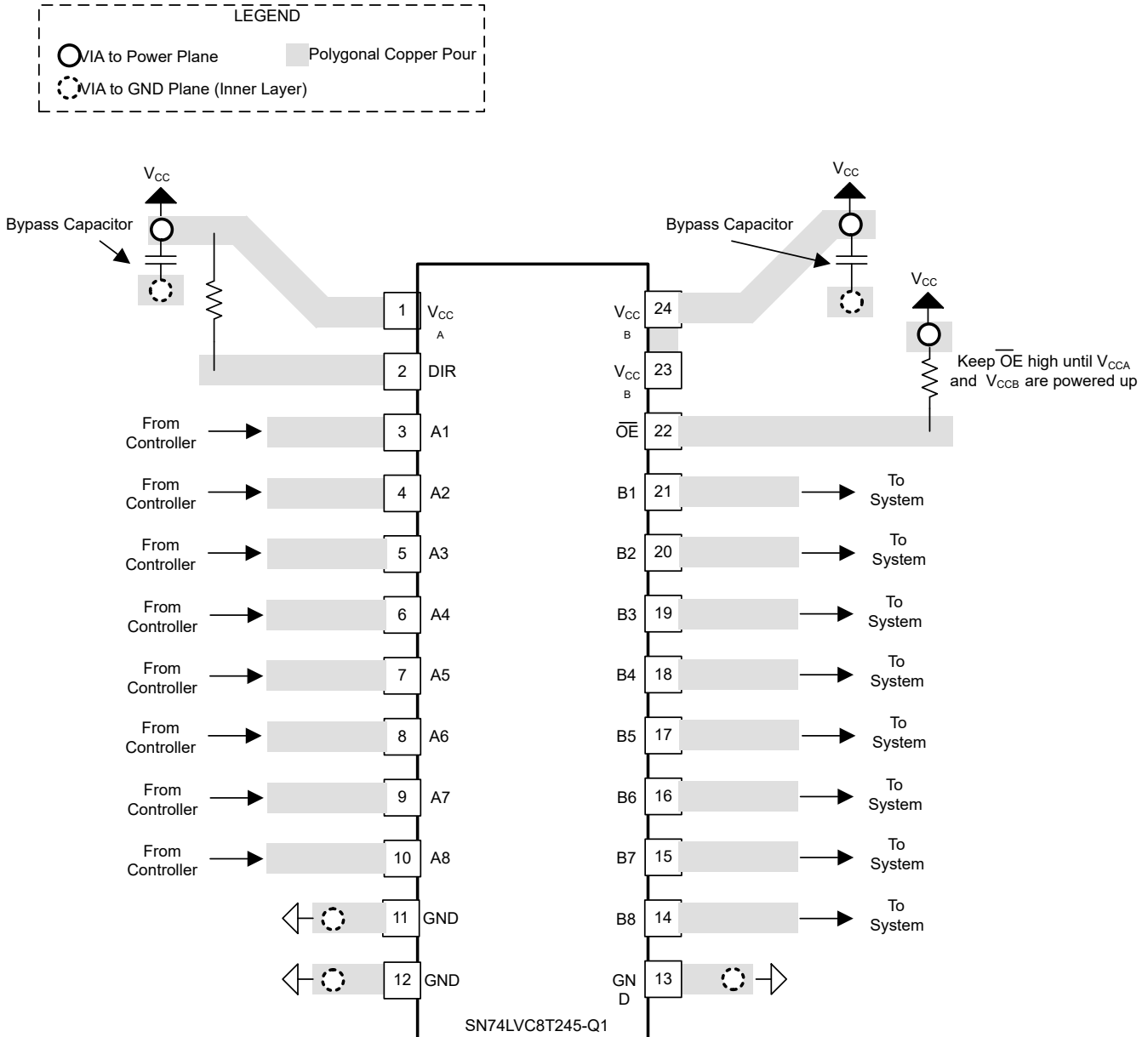
11 Layout

11.1 Layout Guidelines

To ensure reliability of the device, following common printed-circuit board layout guidelines is recommended.

- Bypass capacitors should be used on power supplies.
- Short trace lengths should be used to avoid excessive loading.
- Placing pads on the signal paths for loading capacitors or pullup resistors helps adjust rise and fall times of signals depending on the system requirements.

11.2 Layout Example



11-1. SN74LVC8T245 Layout

12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.com のデバイス製品フォルダを開いてください。「更新の通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

12.2 サポート・リソース

[TI E2E™ サポート・フォーラム](#)は、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

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12.3 Trademarks

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12.4 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

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12.5 用語集

[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
74LVC8T245DBQRG4	ACTIVE	SSOP	DBQ	24	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	LVC8T245	Samples
74LVC8T245RHLRG4	ACTIVE	VQFN	RHL	24	1000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	NH245	Samples
SN74LVC8T245DBQR	ACTIVE	SSOP	DBQ	24	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	LVC8T245	Samples
SN74LVC8T245DBR	ACTIVE	SSOP	DB	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	NH245	Samples
SN74LVC8T245DBRG4	ACTIVE	SSOP	DB	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	NH245	Samples
SN74LVC8T245DGVR	ACTIVE	TVSOP	DGV	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	NH245	Samples
SN74LVC8T245DGVRG4	ACTIVE	TVSOP	DGV	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	NH245	Samples
SN74LVC8T245DWR	ACTIVE	SOIC	DW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVC8T245	Samples
SN74LVC8T245DWRG4	ACTIVE	SOIC	DW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVC8T245	Samples
SN74LVC8T245NSR	ACTIVE	SOP	NS	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVC8T245	Samples
SN74LVC8T245PW	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	NH245	Samples
SN74LVC8T245PWG4	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	NH245	Samples
SN74LVC8T245PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	NH245	Samples
SN74LVC8T245PWRE4	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	NH245	Samples
SN74LVC8T245PWRG4	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	NH245	Samples
SN74LVC8T245RHLR	ACTIVE	VQFN	RHL	24	1000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	NH245	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of ≤ 1000 ppm threshold. Antimony trioxide based flame retardants must also meet the ≤ 1000 ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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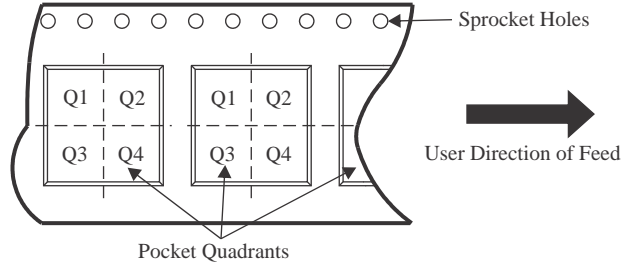
OTHER QUALIFIED VERSIONS OF SN74LVC8T245 :

- Automotive : [SN74LVC8T245-Q1](#)
- Enhanced Product : [SN74LVC8T245-EP](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC8T245DBQR	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74LVC8T245DBR	SSOP	DB	24	2000	330.0	16.4	8.2	8.8	2.5	12.0	16.0	Q1
SN74LVC8T245DBR	SSOP	DB	24	2000	330.0	16.4	8.2	8.8	2.5	12.0	16.0	Q1
SN74LVC8T245DGVR	TVSOP	DGV	24	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LVC8T245DWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
SN74LVC8T245NSR	SOP	NS	24	2000	330.0	24.4	8.3	15.4	2.6	12.0	24.0	Q1
SN74LVC8T245PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
SN74LVC8T245PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
SN74LVC8T245RHLR	VQFN	RHL	24	1000	180.0	12.4	3.8	5.8	1.2	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC8T245DBQR	SSOP	DBQ	24	2500	356.0	356.0	35.0
SN74LVC8T245DBR	SSOP	DB	24	2000	356.0	356.0	35.0
SN74LVC8T245DBR	SSOP	DB	24	2000	356.0	356.0	35.0
SN74LVC8T245DGVR	TVSOP	DGV	24	2000	356.0	356.0	35.0
SN74LVC8T245DWR	SOIC	DW	24	2000	350.0	350.0	43.0
SN74LVC8T245NSR	SOP	NS	24	2000	367.0	367.0	45.0
SN74LVC8T245PWR	TSSOP	PW	24	2000	356.0	356.0	35.0
SN74LVC8T245PWR	TSSOP	PW	24	2000	356.0	356.0	35.0
SN74LVC8T245RHLR	VQFN	RHL	24	1000	210.0	185.0	35.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN74LVC8T245PW	PW	TSSOP	24	60	530	10.2	3600	3.5
SN74LVC8T245PW	PW	TSSOP	24	60	530	10.2	3600	3.5
SN74LVC8T245PWG4	PW	TSSOP	24	60	530	10.2	3600	3.5
SN74LVC8T245PWG4	PW	TSSOP	24	60	530	10.2	3600	3.5

DW (R-PDSO-G24)

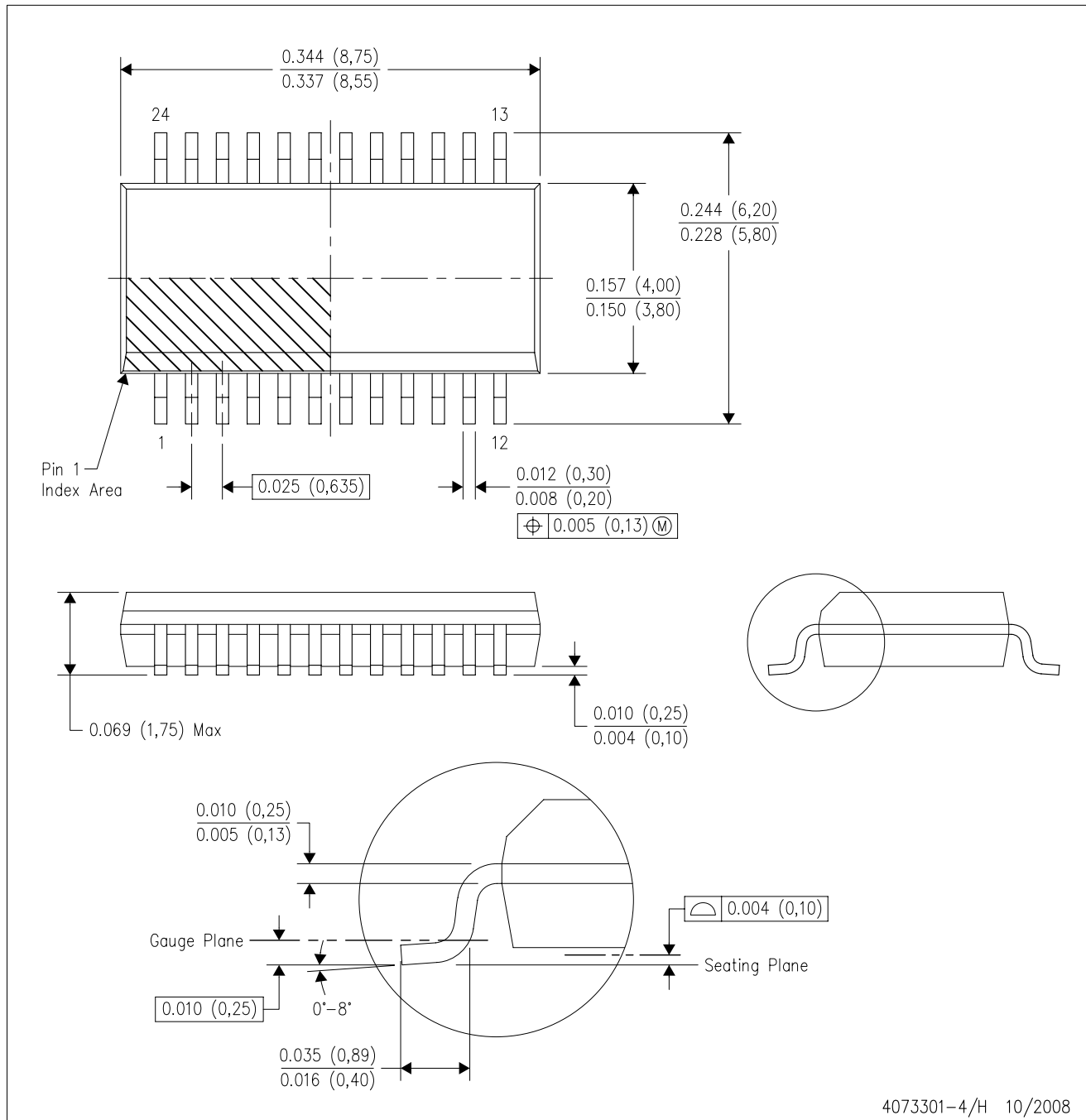
PLASTIC SMALL OUTLINE



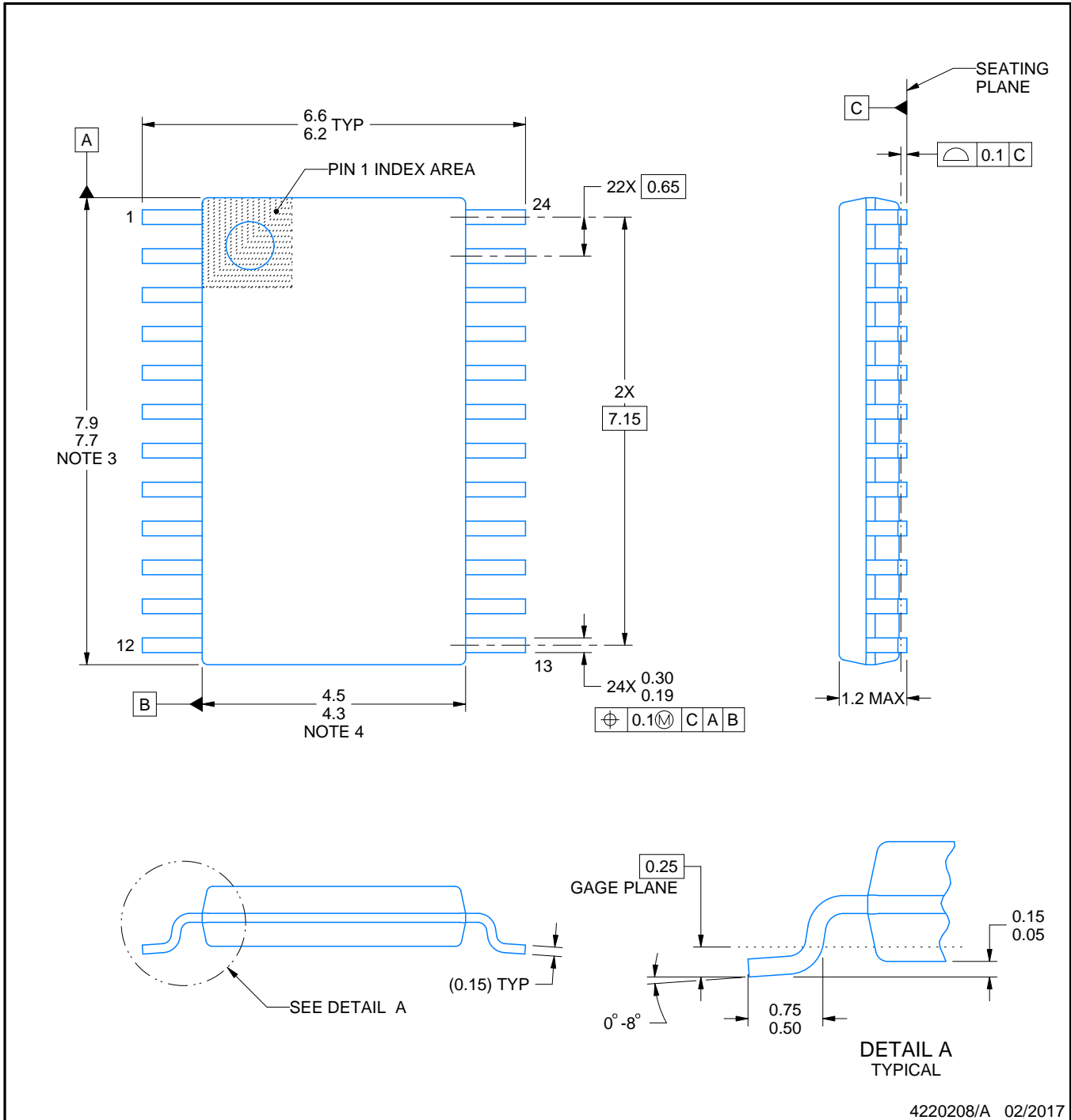
- NOTES:
- A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
 - D. Falls within JEDEC MS-013 variation AD.

DBQ (R-PDSO-G24)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- All linear dimensions are in inches (millimeters).
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
 - Falls within JEDEC MO-137 variation AE.



4220208/A 02/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

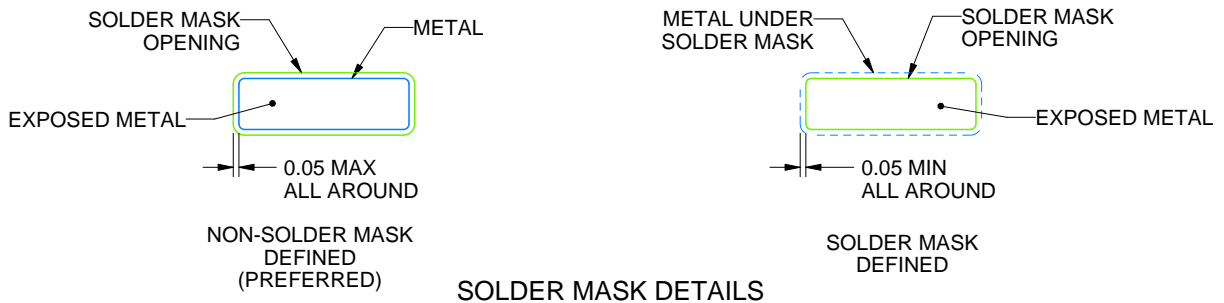
PW0024A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4220208/A 02/2017

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0024A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

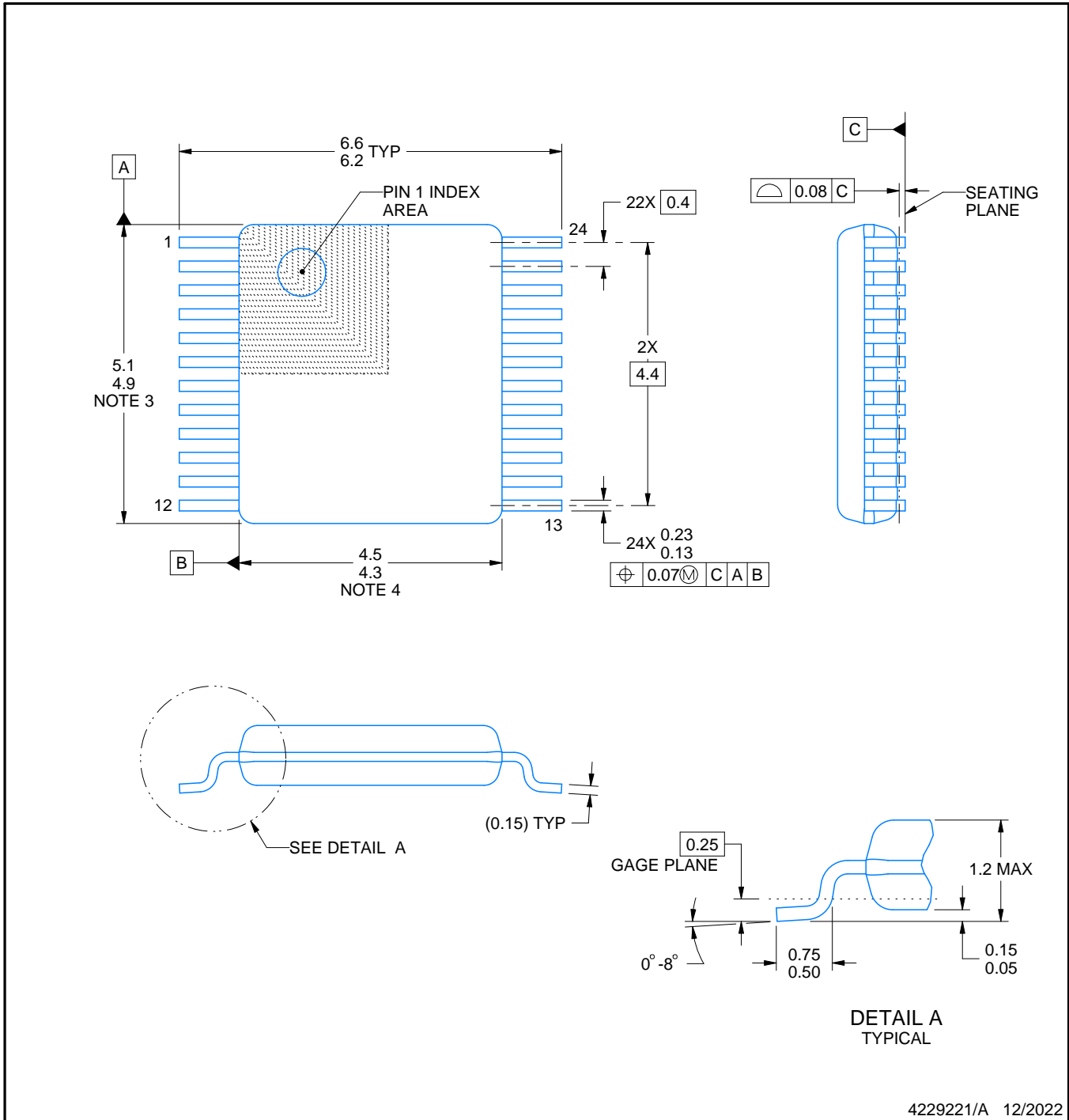
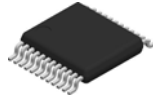
DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



- NOTES: A. All linear dimensions are in millimeters.
 B. This drawing is subject to change without notice.
 C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
 D. Falls within JEDEC MO-150



NOTES:

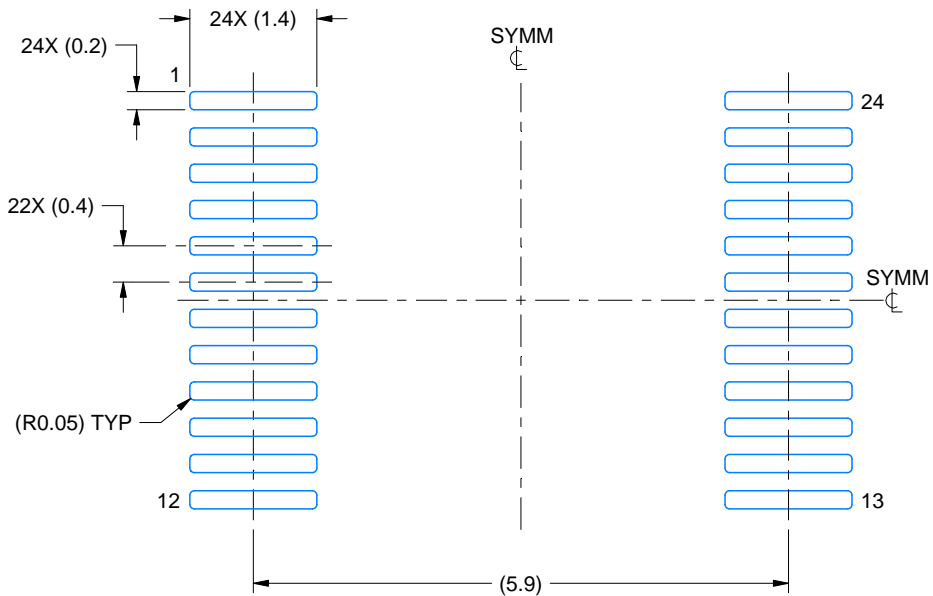
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

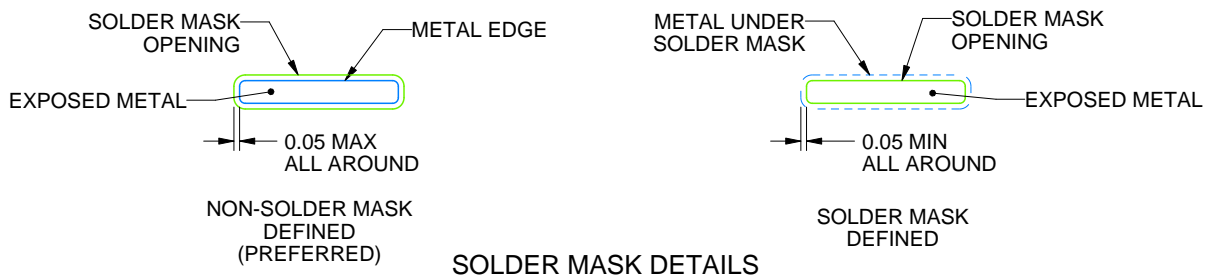
DGV0024A

TVSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 12X



SOLDER MASK DETAILS

4229221/A 12/2022

NOTES: (continued)

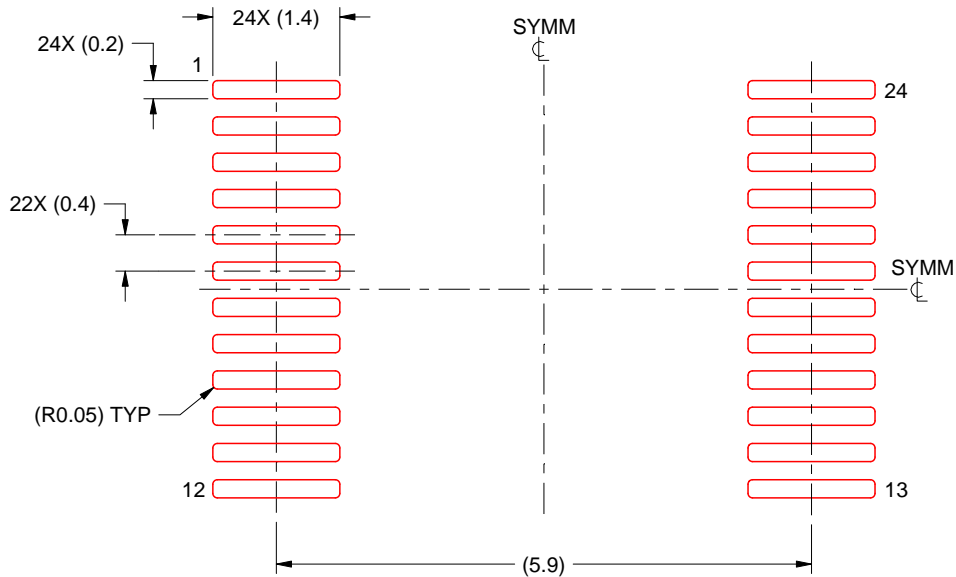
- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DGV0024A

TVSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

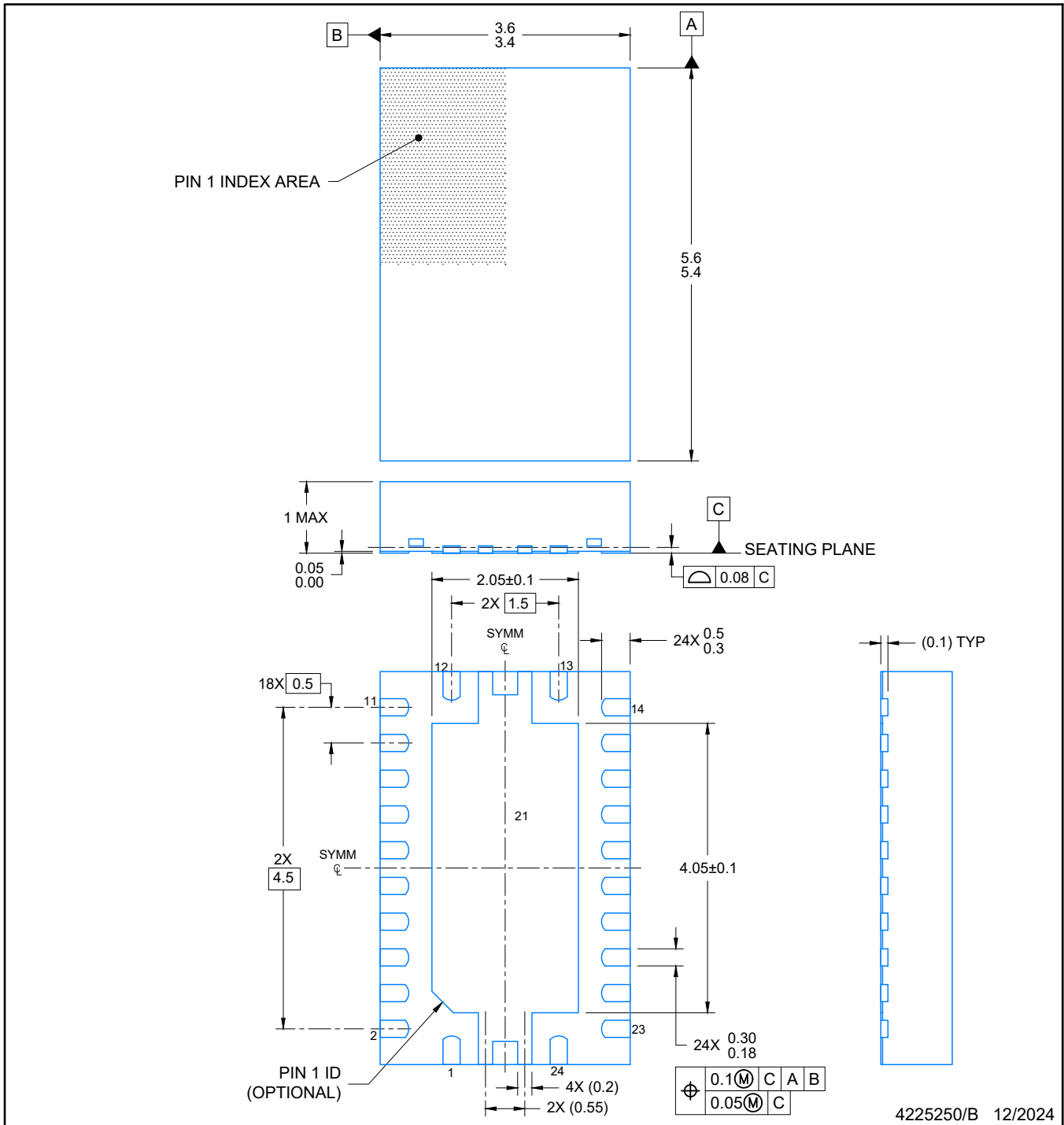


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 12X

4229221/A 12/2022

NOTES: (continued)

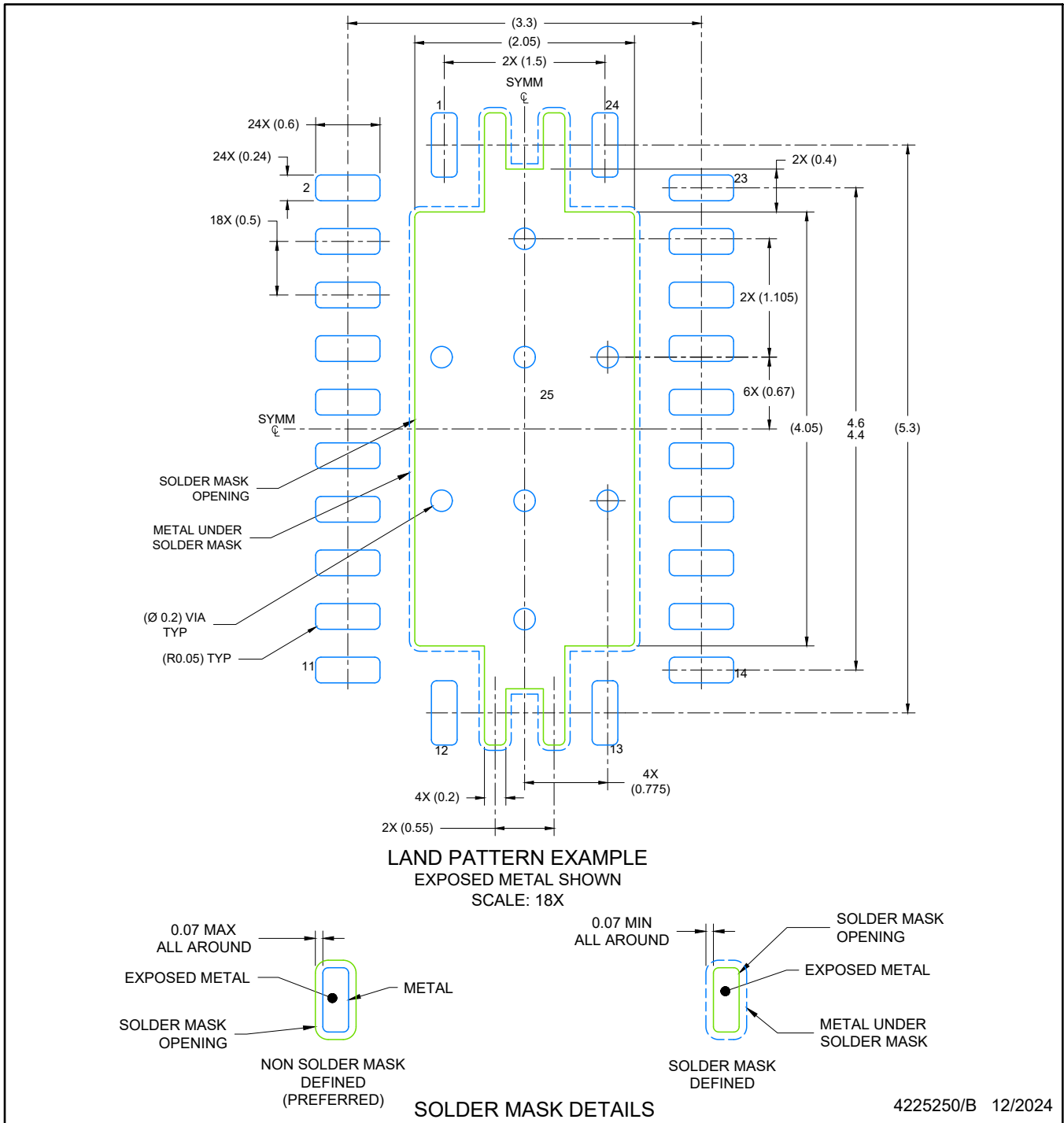
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



4225250/B 12/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



NOTES: (continued)

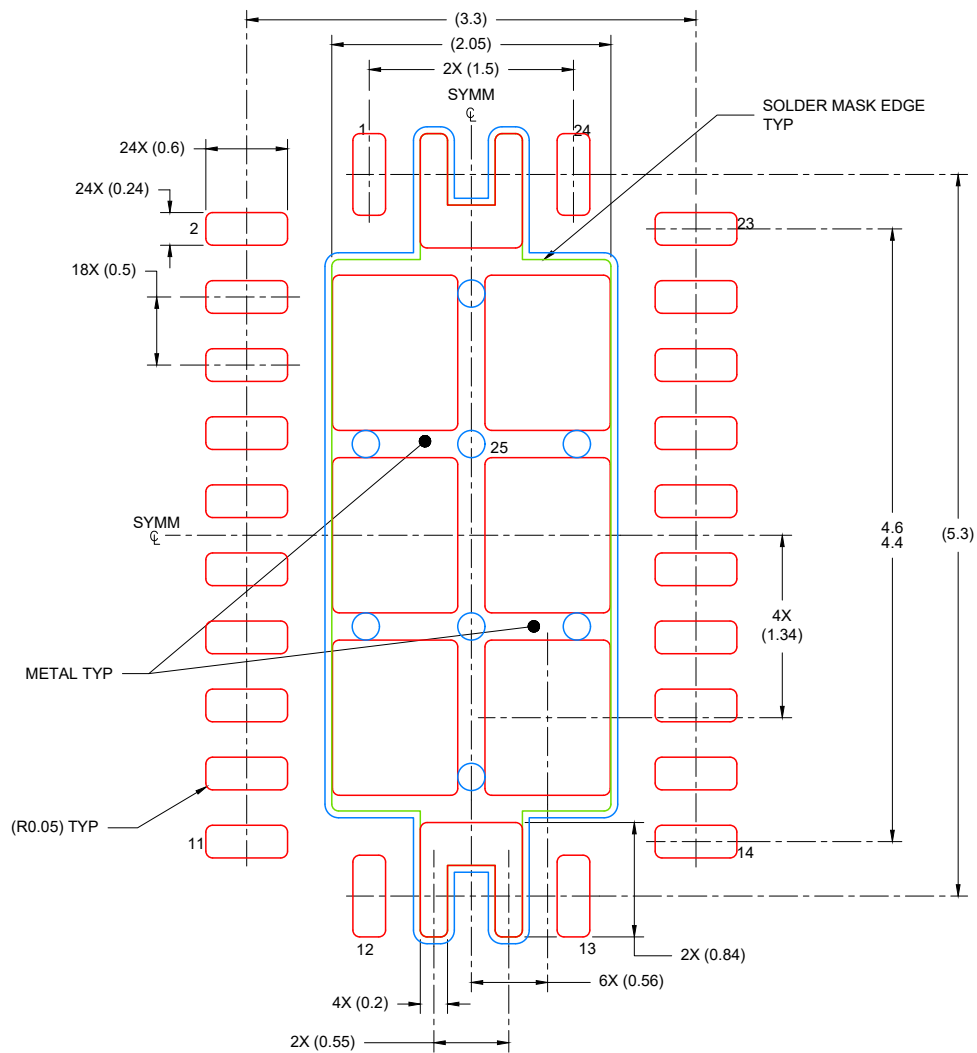
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

VQFN - 1 mm max height

RHL0024A

PLASTIC QUAD FLATPACK- NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
80% PRINTED COVERAGE BY AREA
SCALE: 18X

4225250/B 12/2024

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

MECHANICAL DATA

NS (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14-PINS SHOWN



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

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